

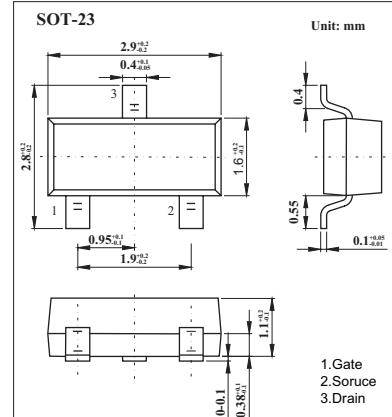
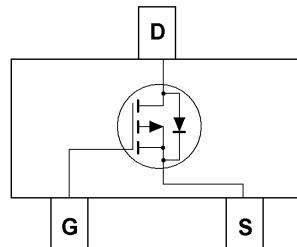
Feature

-20V/-3A, R_{DS(ON)} = 100mΩ(MAX) @V_{GS} = -4.5V.
R_{DS(ON)} = 120mΩ(MAX) @V_{GS} = -2.5V.

Super High dense cell design for extremely low R_{DS(ON)}

Reliable and Rugged

SOT-23 for Surface Mount Package



Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings

T_A=25°C Unless Otherwise noted

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±8	
Continuous Drain Current Ta=25°C	I _D	-3	A
Ta=70°C		-2	
Pulsed Drain Current	I _{DM}	-10	W
Power Dissipation Ta=25°C	P _D	1.5	
Ta=70°C		1.25	°C/W
Thermal Resistance.Junction- to-Ambient *1	R _{thJA}	100	
Thermal Resistance.Junction- to-Ambient *3		166	
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

Electrical Characteristics

T_A=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μ A, V _{GS} =0V	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μ A
		V _{DS} =-20V, V _{GS} =0V, T _J =55°C			-10	
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±8V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250 μ A	-0.45		-1	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-2.8A		105	110	mΩ
		V _{GS} =-2.5V, I _D =-2.0A		115	120	
On state drain current	I _{D(ON)}	V _{GS} =-4.5V, V _{DS} ≤ -5V	-6			A
		V _{GS} =-2.5V, V _{DS} ≤ -5V	-3			
Forward Transconductance	g _F	V _{DS} =-5V, I _D =-2.8A		6.5		S

Marking

Marking	YDs **
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Typical Characteristics

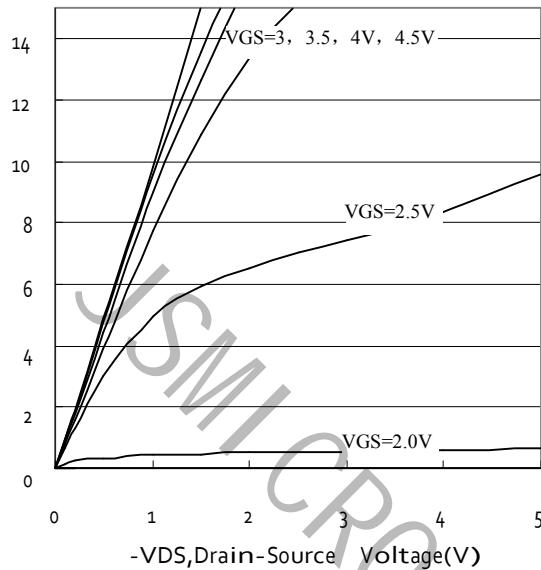


Figure 1. Output Characteristics

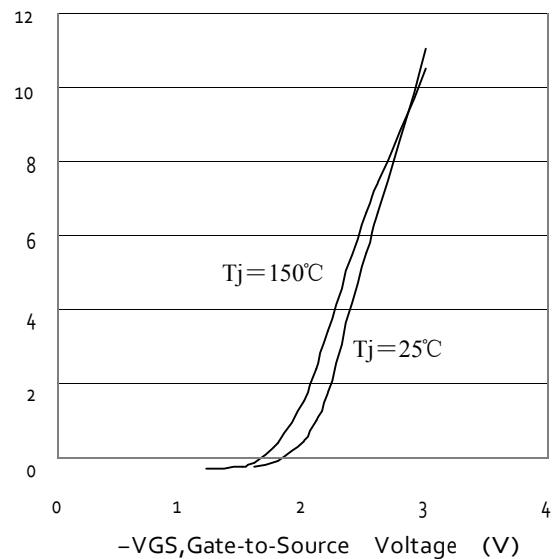


Figure 2. Transfer Characteristics

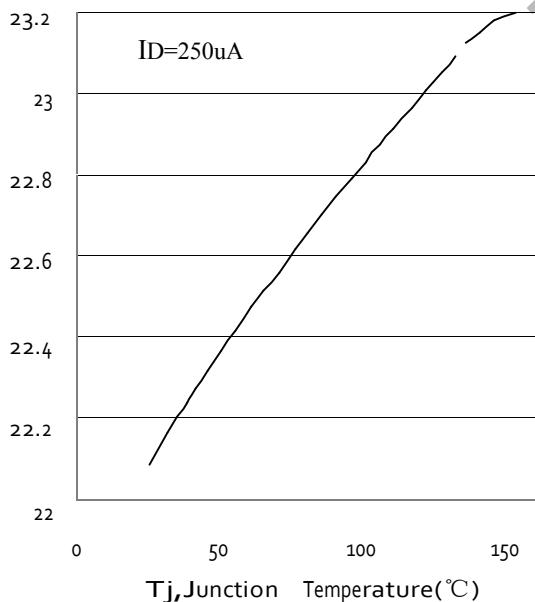


Figure 3. Breakdown Voltage Variation with Temperature

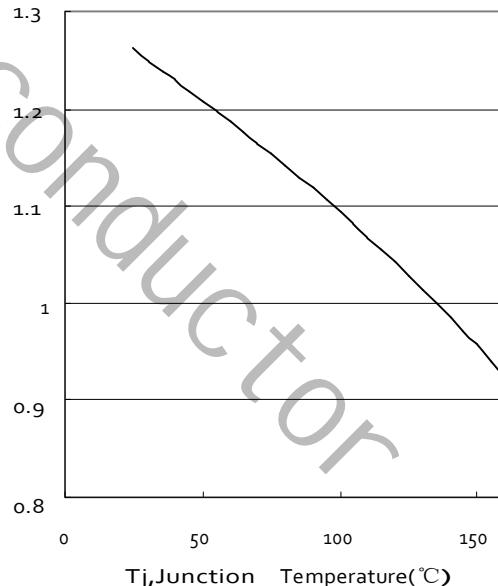


Figure 4. Gate Threshold Variation with Temperature

Typical Characteristics

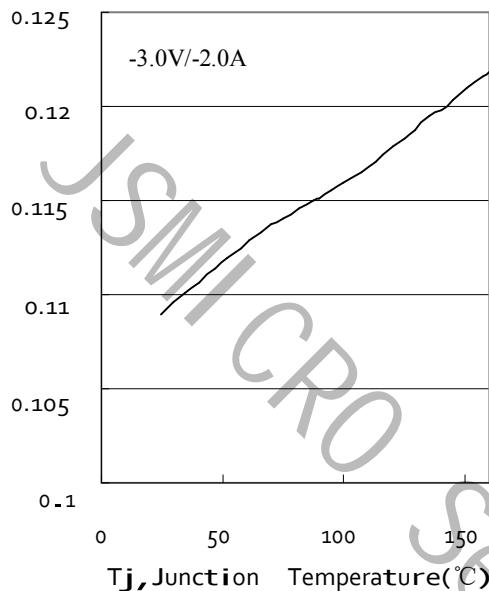


Figure 5. On-Resistance Variation with Temperature

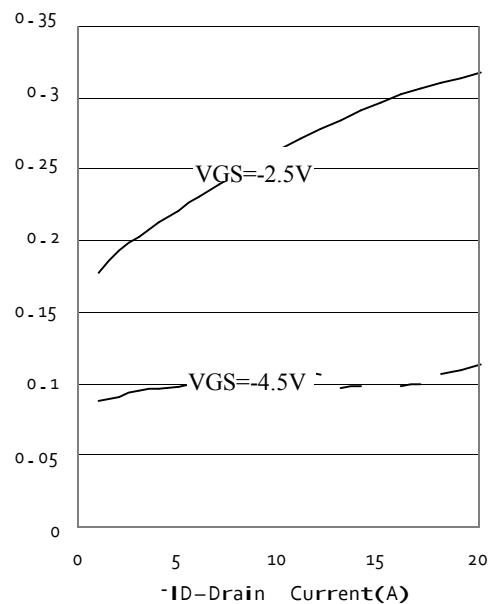


Figure 6. On-Resistance vs. Drain Current

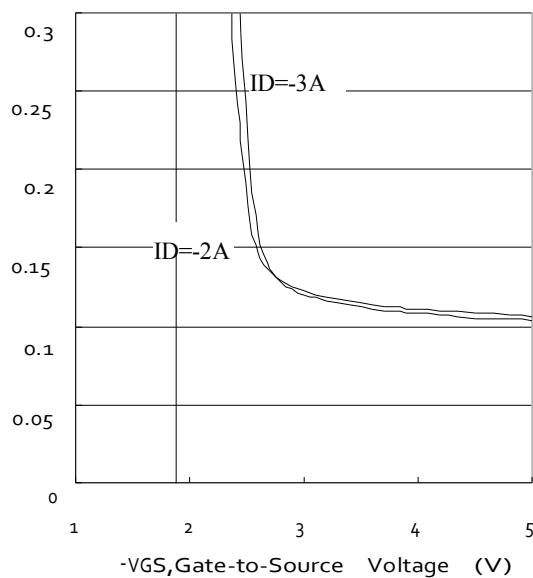


Figure 7 . On-Resistance vs. Gate-to-Source Voltage

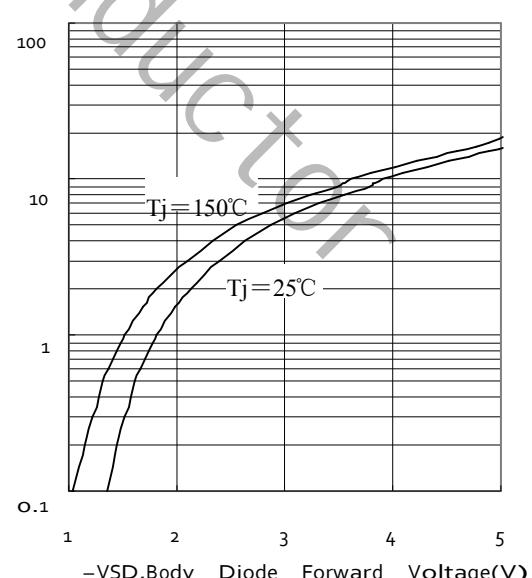
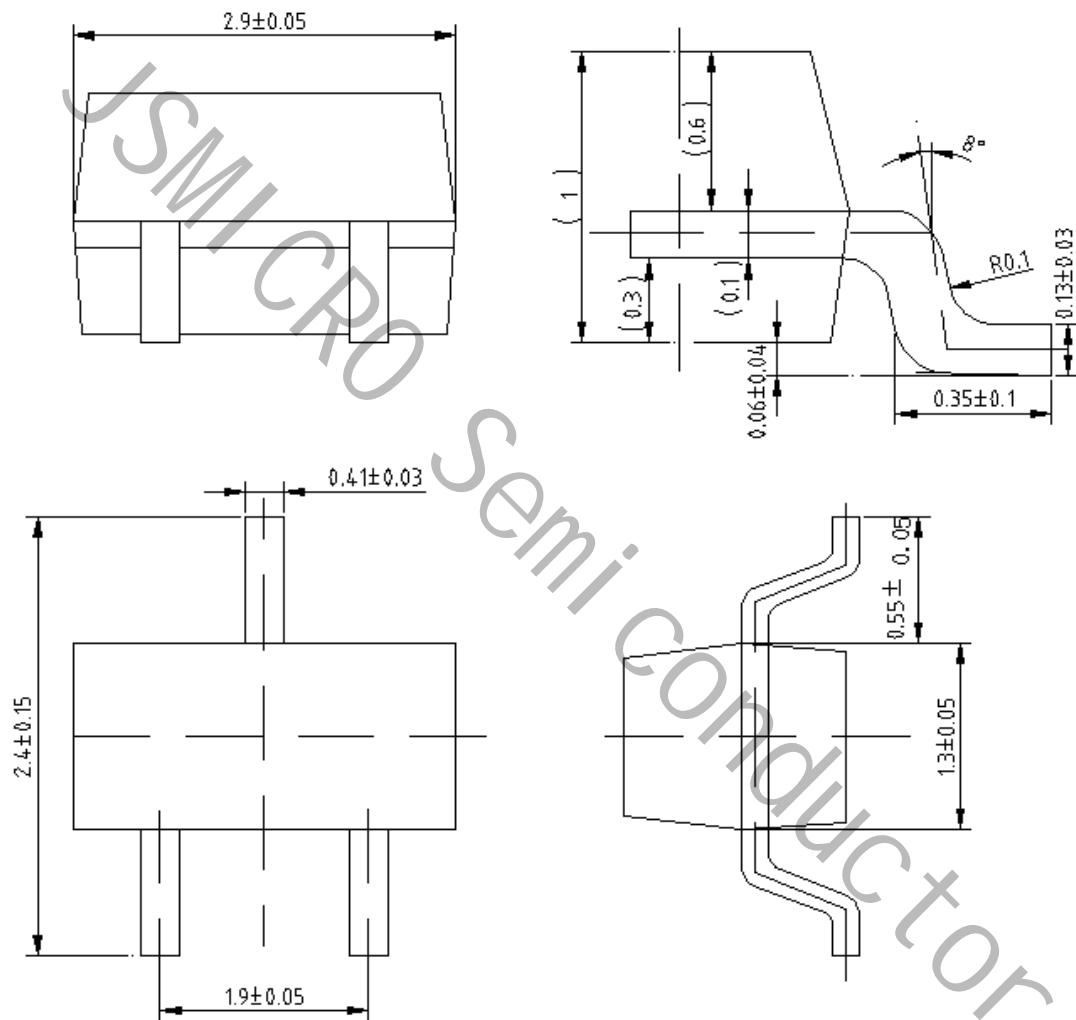


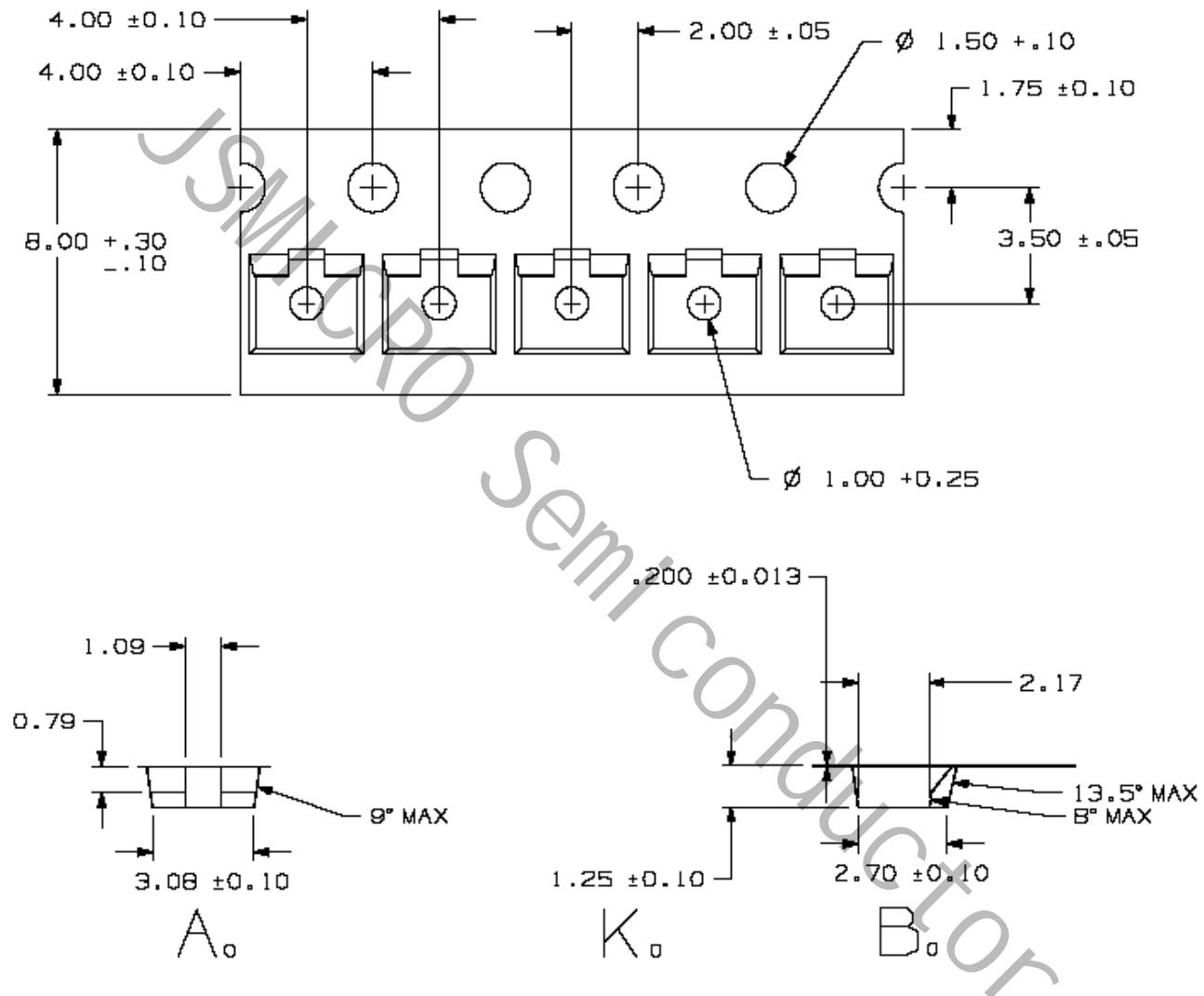
Figure 8 . Source-Drain Diode Forward

Package Outline Dimensions (UNIT: mm)

SOT-23



SOT-23 Carrier Tape



SOT-23 Carrier Reel

